Si APD (avalanche photodiode)

High-speed, high sensitivity photodiodes having an internal gain mechanism
Si APD
High-speed, high sensitivity photodiodes having an internal gain mechanism
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The APD is a high-speed, high-sensitivity photodiode that internally multiplies photocurrent when reverse voltage is applied. The APD, having a signal multiplication function inside its element, achieves higher S/N than the PIN photodiode and can be used in a wide range of applications such as high-accuracy rangefinders and low-light-level detection that use scintillators. Though the APD can detect lower level light than the PIN photodiode, it does require special care and handling such as the need for higher reverse voltage and more detailed consideration of its temperature-dependent gain characteristics.

### Si APD

<table>
<thead>
<tr>
<th>Type</th>
<th>Recommended wavelength (nm)</th>
<th>Peak sensitivity wavelength (nm)</th>
<th>Type no.</th>
<th>Package</th>
<th>Features</th>
<th>Applications</th>
<th>Page</th>
</tr>
</thead>
<tbody>
<tr>
<td>Short wavelength type</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Low-bias operation</td>
<td>200 to 650</td>
<td>620</td>
<td>S12053 series, etc.</td>
<td>Metal</td>
<td>Enhanced sensitivity in the UV to visible region</td>
<td>Low-light-level detection, Analytical instruments</td>
<td>5</td>
</tr>
<tr>
<td>Low terminal capacitance</td>
<td>320 to 650</td>
<td>600</td>
<td>S8664-K series, etc.</td>
<td>Metal, Ceramic</td>
<td></td>
<td></td>
<td>6</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>S8664-55/1010</td>
<td></td>
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<tr>
<td></td>
<td></td>
<td></td>
<td>S8550-02</td>
<td></td>
<td></td>
<td></td>
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<tr>
<td>Near infrared type</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Low-bias operation</td>
<td>600 to 800</td>
<td>800</td>
<td>S12023 series, etc.</td>
<td>Metal</td>
<td>High sensitivity in the near IR region and low bias voltage (operating voltage)</td>
<td>FSO, Optical rangefinders, Optical fiber communication</td>
<td>7</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>S14644 series</td>
<td>Surface mount type</td>
<td>Compact, thin, low cost</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Low temperature coefficient</td>
<td>600 to 800</td>
<td>800</td>
<td>S12060 series, etc.</td>
<td>Metal</td>
<td>Low temperature coefficient of the bias voltage, easy gain adjustment</td>
<td>FSO, Optical rangefinders, Optical fiber communication</td>
<td>9</td>
</tr>
<tr>
<td>900 nm band, low terminal capacitance</td>
<td>800 to 1000</td>
<td>860</td>
<td>S12426 series, etc.</td>
<td>Metal</td>
<td>Enhanced sensitivity in the 900 nm band</td>
<td>Optical rangefinders, Laser radars</td>
<td>10</td>
</tr>
<tr>
<td></td>
<td></td>
<td></td>
<td>S14645-02/05F</td>
<td>Surface mount type</td>
<td>Compact, thin, with filter</td>
<td></td>
<td></td>
</tr>
<tr>
<td>TE-cooled type</td>
<td>400 to 1000</td>
<td>800</td>
<td>S4315 series</td>
<td>Metal</td>
<td>High S/N</td>
<td>Low-light-level detection</td>
<td>11</td>
</tr>
</tbody>
</table>

### APD modules

<table>
<thead>
<tr>
<th>Type</th>
<th>Type no.</th>
<th>Features</th>
<th>Page</th>
</tr>
</thead>
<tbody>
<tr>
<td>Standard type</td>
<td>C12702 series</td>
<td>Contains near infrared type or short wavelength type APD. FC/SMA fiber adapters are also available.</td>
<td>12</td>
</tr>
<tr>
<td>High-sensitivity type</td>
<td>C12703 series</td>
<td>High gain type for low-light-level detection</td>
<td></td>
</tr>
<tr>
<td>High-stability type</td>
<td>C10508-01</td>
<td>Digital temperature compensation type, high stability APD module</td>
<td>13</td>
</tr>
<tr>
<td>High-speed type</td>
<td>C5658</td>
<td>Can be used over a wide frequency range (up to 1 GHz)</td>
<td></td>
</tr>
</tbody>
</table>

### Principle of avalanche multiplication

The photocurrent generation mechanism of the APD is the same as that of a normal photodiode. When light enters a photodiode, electron-hole pairs are generated if the light energy is higher than the band gap energy. The ratio of the number of generated electron-hole pairs to the number of incident photons is defined as the quantum efficiency (QE), expressed in percent (%). The mechanism by which carriers are generated inside an APD is the same as in a photodiode, but the APD is different from a photodiode in that it has a function to multiply the generated carriers.

When electron-hole pairs are generated in the depletion layer of an APD with a reverse voltage applied to the PN junction, the electric field causes the electrons to drift toward the N⁺ side and the holes to drift toward the P⁺ side. The higher the electric field strength, the higher the drift speed of these carriers. However, when the electric field reaches a certain level, the carriers are more likely to collide with the crystal lattice so that the drift speed becomes saturated at a certain speed. If the electric field is increased even further, carriers that escaped the collision with the crystal lattice will have a great deal of energy. When these carriers collide with the crystal lattice, a phenomenon takes place in which new electron-hole pairs are generated. This phenomenon is called ionization. These electron-hole pairs then create additional electron-hole pairs, which generate a chain reaction of ionization.

### Principle of APD operation

Generated carriers produce new electron-hole pairs while being accelerated by high electric field. Newly generated carriers are also accelerated to produce further electron-hole pairs, and this process repeats itself. Gain proportional to the applied reverse bias voltage can be obtained.
**Spectral response (Si APD)** For the absolute sensitivity values, see the individual datasheets.

- **High**
  - 200
  - 400
  - 600
  - 800
  - 1000
  - 1200

**Cutoff frequency vs. recommended wavelength (typical example)**

- **Short wavelength type (Low terminal capacitance)**
- **Near infrared type (Low terminal capacitance)**
- **Short wavelength type (Low-bias operation)**
- **Near infrared type (Low temperature coefficient)**

**Sensitivity vs. response speed (APD modules)**

- **DC to 100 kHz**
  - DC to 10 MHz: $1.5 \times 10^7 \text{ V/W}$
  - DC to 50 kHz to 1 GHz: $2.5 \times 10^7 \text{ V/W}$

- **DC to 10 kHz**
  - DC to 10 MHz: $1.5 \times 10^6 \text{ V/W}$
  - DC to 50 kHz to 1 GHz: $2.5 \times 10^6 \text{ V/W}$

- **DC to 1 kHz**
  - DC to 10 MHz: $1.5 \times 10^5 \text{ V/W}$

4 types available for different photosensitive areas and wavelengths. 4 MHz to 100 MHz $1 \times 10^5 \text{ V/W}$.
These are short wavelength Si APDs with enhanced sensitivity in the UV to visible region. They offer high gain, high sensitivity, and low noise in the short wavelength region. They are suitable for applications such as low-light-level measurement and analytical instruments.

### Low-bias operation

<table>
<thead>
<tr>
<th>Type no.</th>
<th>Effective photosensitive area*1 (mm)</th>
<th>Spectral response range (nm)</th>
<th>Breakdown voltage max. I0=100 μA (V)</th>
<th>Temp. coefficient of breakdown voltage (V/°C)</th>
<th>Cutoff frequency*1(2) RL=50 Ω (MHz)</th>
<th>Rise time*1(2) RL=50 Ω (ns)</th>
<th>Terminal capacitance*1(2) (pF)</th>
<th>Gain λ=650 nm</th>
<th>Package</th>
</tr>
</thead>
<tbody>
<tr>
<td>S12053-02</td>
<td>φ0.2</td>
<td>200 to 1000</td>
<td>200</td>
<td>0.14</td>
<td>900</td>
<td>0.4</td>
<td>2</td>
<td></td>
<td></td>
</tr>
<tr>
<td>S12053-05</td>
<td>φ0.5</td>
<td>200 to 1000</td>
<td>200</td>
<td>0.14</td>
<td>400</td>
<td>0.9</td>
<td>5</td>
<td></td>
<td></td>
</tr>
<tr>
<td>S12053-10</td>
<td>φ1.0</td>
<td>200 to 1000</td>
<td>200</td>
<td>0.14</td>
<td>250</td>
<td>1.5</td>
<td>15</td>
<td></td>
<td></td>
</tr>
<tr>
<td>S9075</td>
<td>φ1.5</td>
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<td></td>
</tr>
<tr>
<td>S5344</td>
<td>φ3.0</td>
<td></td>
<td></td>
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<tr>
<td>S5345</td>
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<td></td>
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<td></td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

*1: Area in which a typical gain can be obtained  
*2: Value obtained when operated at the gain indicated in the table

### Spectral response

![Spectral response graph](image)

### Quantum efficiency vs. wavelength

![Quantum efficiency graph](image)

### Gain vs. reverse voltage

![Gain vs. reverse voltage graph](image)
### Low terminal capacitance

<table>
<thead>
<tr>
<th>Type no.</th>
<th>Effective photosensitive area*3 (mm)</th>
<th>Spectral response range (nm)</th>
<th>Breakdown voltage max. (V)</th>
<th>Temp. coefficient of breakdown voltage (V/°C)</th>
<th>Cutoff frequency*4 RL=50 Ω (MHz)</th>
<th>Rise time*4 RL=50 Ω (ns)</th>
<th>Terminal capacitance*4 (pF)</th>
<th>Gain λ=420 nm</th>
<th>Package</th>
</tr>
</thead>
<tbody>
<tr>
<td>S8664-02K</td>
<td>φ0.2</td>
<td>320 to 1000</td>
<td>500</td>
<td>0.78</td>
<td>700</td>
<td>0.5</td>
<td>0.8</td>
<td></td>
<td>TO-5</td>
</tr>
<tr>
<td>S8664-05K</td>
<td>φ0.5</td>
<td></td>
<td></td>
<td></td>
<td>680</td>
<td>0.52</td>
<td>1.6</td>
<td></td>
<td>TO-8</td>
</tr>
<tr>
<td>S8664-10K</td>
<td>φ1.0</td>
<td></td>
<td></td>
<td></td>
<td>530</td>
<td>0.66</td>
<td>4</td>
<td></td>
<td>Ceramic</td>
</tr>
<tr>
<td>S8664-20K</td>
<td>φ2.0</td>
<td></td>
<td></td>
<td></td>
<td>280</td>
<td>1.3</td>
<td>11</td>
<td></td>
<td></td>
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<tr>
<td>S8664-30K</td>
<td>φ3.0</td>
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<td></td>
<td></td>
<td>140</td>
<td>2.5</td>
<td>22</td>
<td></td>
<td></td>
</tr>
<tr>
<td>S8664-50K</td>
<td>φ5.0</td>
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<td></td>
<td></td>
<td>60</td>
<td>6</td>
<td>55</td>
<td></td>
<td></td>
</tr>
<tr>
<td>S8664-55</td>
<td>5 × 5</td>
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<td></td>
<td>40</td>
<td>9</td>
<td>80</td>
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</tr>
<tr>
<td>S8664-1010</td>
<td>10 × 10</td>
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<td></td>
<td>11</td>
<td>32</td>
<td>270</td>
<td></td>
<td></td>
</tr>
<tr>
<td>S11051-20</td>
<td>φ2.0</td>
<td>266</td>
<td></td>
<td></td>
<td>250</td>
<td>1.4</td>
<td>11</td>
<td></td>
<td>TO-8</td>
</tr>
</tbody>
</table>

*3: Area in which a typical gain can be obtained  
*4: Value obtained when operated at the gain indicated in the table

### 4 × 8 element array

<table>
<thead>
<tr>
<th>Type no.</th>
<th>Effective photosensitive area*3 (× 32 elements)</th>
<th>Spectral response range (nm)</th>
<th>Breakdown voltage max. (V)</th>
<th>Temp. coefficient of breakdown voltage (V/°C)</th>
<th>Cutoff frequency*4 RL=50 Ω (MHz)</th>
<th>Rise time*4 RL=50 Ω (ns)</th>
<th>Terminal capacitance*4 (pF)</th>
<th>Gain λ=420 nm</th>
<th>Package</th>
</tr>
</thead>
<tbody>
<tr>
<td>S8550-02</td>
<td>1.6 × 1.6 (× 32 elements)</td>
<td>320 to 1000</td>
<td>500</td>
<td>0.78</td>
<td>250</td>
<td>9</td>
<td>50 (per element)</td>
<td></td>
<td>Ceramic</td>
</tr>
</tbody>
</table>

### Spectral response

[Graph: Spectral response vs. Wavelength]

### Quantum efficiency vs. wavelength

[Graph: Quantum efficiency vs. Wavelength]

### Gain vs. reverse voltage

[Graph: Gain vs. Reverse Voltage]
Near infrared type Si APD

Low-bias operation

These are near infrared Si APDs that operate with low bias voltage. Since high gain can be attained with a bias voltage of 200 V or less, they are suitable for applications such as FSO, laser radar, and optical fiber communication.

<table>
<thead>
<tr>
<th>Type no.</th>
<th>Effective photosensitive area*1 (mm)</th>
<th>Spectral response range (nm)</th>
<th>Breakdown voltage max. Id=100 μA (V)</th>
<th>Temp. coefficient of breakdown voltage (V/°C)</th>
<th>Cutoff frequency*2 RL=50 Ω (MHz)</th>
<th>Terminal capacitance*2 (pF)</th>
<th>Gain λ=800 nm</th>
<th>Package</th>
</tr>
</thead>
<tbody>
<tr>
<td>S12023-02</td>
<td>φ0.2</td>
<td>400 to 1000</td>
<td>200</td>
<td>0.65</td>
<td>1000</td>
<td>1</td>
<td></td>
<td></td>
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<tr>
<td>S12023-05</td>
<td></td>
<td></td>
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<td></td>
</tr>
<tr>
<td>S12051</td>
<td>φ0.5</td>
<td></td>
<td>900</td>
<td>2</td>
<td></td>
<td>100</td>
<td>TO-18</td>
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<td>S12086</td>
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<tr>
<td>S12023-10</td>
<td>φ1.0</td>
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<td>600</td>
<td>6</td>
<td></td>
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<td></td>
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</tr>
<tr>
<td>S12023-10A</td>
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<tr>
<td>S3884</td>
<td>φ1.5</td>
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<td>400</td>
<td>10</td>
<td>100</td>
<td></td>
<td>TO-5</td>
<td></td>
</tr>
<tr>
<td>S2384</td>
<td>φ3.0</td>
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<td>120</td>
<td>40</td>
<td>60</td>
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<td></td>
</tr>
<tr>
<td>S2385</td>
<td>φ5.0</td>
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<td>40</td>
<td>95</td>
<td>40</td>
<td></td>
<td>TO-8</td>
<td></td>
</tr>
</tbody>
</table>

Surface mount type

These are low cost, small size Si APDs with a surface-mount plastic package suitable for mass production.

<table>
<thead>
<tr>
<th>Type no.</th>
<th>Effective photosensitive area*1 (mm)</th>
<th>Spectral response range (nm)</th>
<th>Breakdown voltage max. Id=100 μA (V)</th>
<th>Temp. coefficient of breakdown voltage (V/°C)</th>
<th>Cutoff frequency*2 RL=50 Ω (MHz)</th>
<th>Terminal capacitance*2 (pF)</th>
<th>Gain λ=800 nm</th>
<th>Package</th>
</tr>
</thead>
<tbody>
<tr>
<td>S14644-02</td>
<td>φ0.2</td>
<td></td>
<td>180</td>
<td>0.63</td>
<td>1200</td>
<td>0.6</td>
<td></td>
<td>Plastic</td>
</tr>
<tr>
<td>S14644-05</td>
<td>φ0.5</td>
<td>400 to 1000</td>
<td></td>
<td></td>
<td>1000</td>
<td>1.6</td>
<td>100</td>
<td>Plastic</td>
</tr>
<tr>
<td>S14643-02</td>
<td>φ0.2</td>
<td></td>
<td>120</td>
<td>0.42</td>
<td>2000</td>
<td>0.7</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

*1: Area in which a typical gain can be obtained
*2: Value obtained when operated at the gain indicated in the table
### Spectral response

[S12023 series, S12051, S12086, S3884, S2384, S2385]

[S14643-02, S14644 series]

![Spectral response graphs](image)

### Quantum efficiency vs. wavelength

[S12023 series, S12051, S12086, S3884, S2384, S2385]

[S14643-02, S14644 series]

![Quantum efficiency graphs](image)

### Gain vs. reverse voltage

[S12023/S14644 series, S12051, S12086, S3884, S2384, S2385]

[S14643-02]

![Gain vs. reverse voltage graphs](image)
These are near infrared Si APDs featuring low temperature coefficient of the bias voltage. They produce stable gain over a wide temperature range. They are suitable for applications such as FSO, laser radar, and optical fiber communication.

<table>
<thead>
<tr>
<th>Type no.</th>
<th>Effective photosensitive area*1 (mm)</th>
<th>Spectral response range (nm)</th>
<th>Breakdown voltage max. ID=100 μA (V)</th>
<th>Temp. coefficient of breakdown voltage (V/°C)</th>
<th>Cutoff frequency*2 RL=50 Ω (MHz)</th>
<th>Terminal capacitance*2 (pF)</th>
<th>Gain λ=800 nm</th>
<th>Package</th>
</tr>
</thead>
<tbody>
<tr>
<td>S12060-02</td>
<td>φ0.2</td>
<td></td>
<td>400 to 1000</td>
<td>300</td>
<td>0.4</td>
<td></td>
<td>100</td>
<td>TO-18</td>
</tr>
<tr>
<td>S12060-05</td>
<td>φ0.5</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td>900</td>
<td>2.5</td>
</tr>
<tr>
<td>S12060-10</td>
<td>φ1.0</td>
<td></td>
<td>400 to 1000</td>
<td>300</td>
<td>0.4</td>
<td></td>
<td>100</td>
<td>TO-18</td>
</tr>
<tr>
<td>S6045-04</td>
<td>φ1.5</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td>350</td>
<td>12</td>
</tr>
<tr>
<td>S6045-05</td>
<td>φ3.0</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td>80</td>
<td>50</td>
</tr>
<tr>
<td>S6045-06</td>
<td>φ5.0</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td>35</td>
<td>120</td>
</tr>
</tbody>
</table>

*1: Area in which a typical gain can be obtained
*2: Value obtained when operated at the gain indicated in the table

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**Spectral response**

![Spectral response graph](image)

**Quantum efficiency vs. wavelength**

![Quantum efficiency graph](image)

**Gain vs. reverse voltage**

![Gain vs. reverse voltage graph](image)
This series is used in laser radar and other applications. It features a gradual curve of gain versus reverse voltage curve, providing stable operation.

### 900 nm band, low terminal capacitance

The small, thin leadless package allows reducing the mounting area on a printed circuit board. The S14645-02F and S14645-05F have an on-chip filter matched to a 900 nm light source.

#### Surface mount type

The small, thin leadless package allows reducing the mounting area on a printed circuit board. The S14645-02F and S14645-05F have an on-chip filter matched to a 900 nm light source.

### Table: Specifications

<table>
<thead>
<tr>
<th>Type no.</th>
<th>Effective photosensitive area*D (mm)</th>
<th>Spectral response range (nm)</th>
<th>Breakdown voltage max. ID=100 μA (V)</th>
<th>Temp. coefficient of breakdown voltage (V/°C)</th>
<th>Cutoff frequency** RL=50 Ω (MHz)</th>
<th>Terminal capacitance*** (pF)</th>
<th>Gain λ=900 nm</th>
<th>Package</th>
</tr>
</thead>
<tbody>
<tr>
<td>S12426-02</td>
<td>φ0.2</td>
<td>400 to 1100</td>
<td>200</td>
<td>1.1</td>
<td>650</td>
<td>0.5</td>
<td></td>
<td>TO-18</td>
</tr>
<tr>
<td>S12426-05</td>
<td>φ0.5</td>
<td>400 to 1100</td>
<td>300</td>
<td>1.1</td>
<td>600</td>
<td>1.1</td>
<td></td>
<td>100</td>
</tr>
<tr>
<td>S9251-10</td>
<td>φ1.0</td>
<td>400 to 1100</td>
<td>350</td>
<td>1.85</td>
<td>380</td>
<td>1.9</td>
<td></td>
<td>TO-5</td>
</tr>
<tr>
<td>S9251-15</td>
<td>φ1.5</td>
<td>400 to 1100</td>
<td>350</td>
<td>3.6</td>
<td>350</td>
<td>3.6</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

### Notes:

*D: Area in which a typical gain can be obtained
**: Value obtained when operated at the gain indicated in the table

### Spectral response

#### S12426/S14645 series

(Typ. T=25 °C, M=100 at λ=900 nm)

#### S9251 series

(Typ. T=25 °C, M at 860 nm)

### Gain vs. reverse voltage

#### S12426/S14645 series

(Typ. λ=900 nm)
The S4315 series is a low-bias operation thermoelectrically-cooled type APD capable of high accuracy detection.

<table>
<thead>
<tr>
<th>Type no.</th>
<th>Cooling temperature ΔT (°C)</th>
<th>Built-in APD</th>
<th>Effective photosensitive area*1 (mm)</th>
<th>Spectral response range (nm)</th>
<th>Breakdown voltage max. I0=100 μA (V)</th>
<th>Cutoff frequency*2 RL=50Ω (MHz)</th>
<th>Terminal capacitance*2 (pF)</th>
<th>Gain λ=800 nm</th>
<th>Package</th>
</tr>
</thead>
<tbody>
<tr>
<td>S4315</td>
<td>40</td>
<td>S12023-02</td>
<td>φ0.2</td>
<td>400 to 1000</td>
<td>1000</td>
<td>1</td>
<td>100</td>
<td></td>
<td></td>
</tr>
<tr>
<td>S4315-01</td>
<td></td>
<td>S12023-05</td>
<td>φ0.5</td>
<td>400 to 1000</td>
<td>900</td>
<td>2</td>
<td>100</td>
<td></td>
<td>TO-8</td>
</tr>
<tr>
<td>S4315-02</td>
<td></td>
<td>S12023-10</td>
<td>φ1.0</td>
<td>400 to 1000</td>
<td>600</td>
<td>6</td>
<td>100</td>
<td></td>
<td></td>
</tr>
<tr>
<td>S4315-04</td>
<td></td>
<td>S2384</td>
<td>φ3.0</td>
<td>400 to 1000</td>
<td>120</td>
<td>40</td>
<td>60</td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

*1: Area in which a typical gain can be obtained
*2: Value obtained when operated at the gain indicated in the table
APD modules

Standard type

The APD module consists of an amplifier and bias power supply assembled in a compact form to facilitate the use of the Si APD. Running on a +5 V power supply, it can be used for a variety of light detection applications up to 100 MHz of frequency bandwidth.

Near infrared type

Features
- Peak sensitivity wavelength: 800 nm
- Wide bandwidth
- Optical fiber adapters are also available. (sold separately).

Applications
- Si APD evaluation
- FSO
- Barcode readers
- Laser radars
- Optical rangefinders
- Optical communication

<table>
<thead>
<tr>
<th>Type no.</th>
<th>Effective photosensitive area*3 (mm)</th>
<th>Built-in APD</th>
<th>Cutoff frequency</th>
<th>Photoelectric conversion sensitivity M=30, λ=800 nm (V/W)</th>
<th>Minimum detection limit M=30, λ=800 nm (nW rms)</th>
<th>Temperature stability of gain 25 ± 10 °C (%)</th>
<th>Supply voltage (V)</th>
</tr>
</thead>
<tbody>
<tr>
<td>C12702-03</td>
<td>ϕ1.0 S12023-10</td>
<td></td>
<td>4 kHz</td>
<td>-6.8 × 10⁴</td>
<td>3</td>
<td>±5 max.</td>
<td>+5</td>
</tr>
<tr>
<td>C12702-04</td>
<td>ϕ3.0 S2384</td>
<td></td>
<td>4 kHz</td>
<td>-2.3 × 10⁴</td>
<td>3.6</td>
<td>+5</td>
<td>+5</td>
</tr>
</tbody>
</table>

Short wavelength type

Features
- Peak sensitivity wavelength: 620 nm
- Wide bandwidth
- Optical fiber adapters are also available (sold separately).

Applications
- Si APD evaluation
- Film scanners
- Laser monitoring

<table>
<thead>
<tr>
<th>Type no.</th>
<th>Effective photosensitive area*3 (mm)</th>
<th>Built-in APD</th>
<th>Cutoff frequency</th>
<th>Photoelectric conversion sensitivity M=30, λ=620 nm (V/W)</th>
<th>Minimum detection limit M=30, λ=620 nm (nW rms)</th>
<th>Temperature stability of gain 25 ± 10 °C (%)</th>
<th>Supply voltage (V)</th>
</tr>
</thead>
<tbody>
<tr>
<td>C12702-11</td>
<td>ϕ1.0 S1205-10</td>
<td></td>
<td>4 kHz</td>
<td>-2.5 × 10⁴</td>
<td>5</td>
<td>±5 max.</td>
<td>+5</td>
</tr>
<tr>
<td>C12702-12</td>
<td>ϕ3.0 S5344</td>
<td></td>
<td>4 kHz</td>
<td>-1.9 × 10⁴</td>
<td>6.3</td>
<td>+5</td>
<td>+5</td>
</tr>
</tbody>
</table>

High-sensitivity type

These are high-gain APD modules suitable for low-light-level detection. They can be used for DC light detection.

Features
- Low-light-level detection
- DC light detection
- High gain

Applications
- Si APD evaluation
- Fluorescence measurement
- Barcode readers
- Particle counters
- Film scanners

<table>
<thead>
<tr>
<th>Type no.</th>
<th>Effective photosensitive area*3 (mm)</th>
<th>Internal APD</th>
<th>Cutoff frequency</th>
<th>Photoelectric conversion sensitivity M=30, λ=800 nm (V/W)</th>
<th>Minimum detection limit M=30, λ=800 nm (nW rms)</th>
<th>Temperature stability of gain 25 ± 10 °C (%)</th>
<th>Supply voltage (V)</th>
</tr>
</thead>
<tbody>
<tr>
<td>C12703</td>
<td>ϕ1.5 S3884</td>
<td>DC</td>
<td>10 MHz</td>
<td>1.5 × 10⁶</td>
<td>0.63</td>
<td>±5 max.</td>
<td>±12</td>
</tr>
<tr>
<td>C12703-01</td>
<td>ϕ3.0 S2384</td>
<td>100 kHz</td>
<td>-1.5 × 10³</td>
<td>0.0063</td>
<td>±5 max.</td>
<td>±12</td>
<td></td>
</tr>
</tbody>
</table>

*3: Area in which a typical gain can be obtained
High-stability type

The C10508-01 consists of an APD, current-voltage converter, high-voltage power supply circuit as well as a microcontroller for adjusting the APD gain and controlling temperature compensation with high accuracy. This makes it easy to adjust the APD gain and even at high gain, stable detection is possible even under temperature fluctuating conditions.

Features
- Gain: adjustable by switch or PC command
- Gain temperature stability: ±5% or less (Gain=250, Ta=0 °C to +40 °C)
- Easy handling: only ±5 V power supply

Features
- Gain: adjustable by switch or PC command
- Gain temperature stability: ±5% or less (Gain=250, Ta=0 °C to +40 °C)
- Easy handling: only ±5 V power supply

Applications
- Si APD evaluation
- Power meters
- Low-light-level detection

<table>
<thead>
<tr>
<th>Type no.</th>
<th>Effective photosensitive area* (mm)</th>
<th>Internal APD</th>
<th>Cutoff frequency</th>
<th>Photoelectric conversion sensitivity M=250, λ=800 nm (V/W)</th>
<th>Minimum detection limit M=250, λ=800 nm (pW rms)</th>
<th>Temperature stability of gain 0 to 40 °C (%)</th>
<th>Supply voltage (V)</th>
</tr>
</thead>
<tbody>
<tr>
<td>C10508-01</td>
<td>φ1.0</td>
<td>S12023-10A</td>
<td>DC, 10 MHz</td>
<td>1.25 × 10^7</td>
<td>63</td>
<td>±5 max.</td>
<td>±5</td>
</tr>
</tbody>
</table>

FC/SMA fiber adapter (sold separately)

FC or SMA fiber adapters can be attached to the following APD modules to allow FC or SMA optical fiber cables to be connected to the modules.

<table>
<thead>
<tr>
<th>APD module</th>
<th>FC fiber adapter</th>
<th>SMA fiber adapter</th>
</tr>
</thead>
<tbody>
<tr>
<td>C12702-03</td>
<td>A8407-18</td>
<td>A8424-18</td>
</tr>
<tr>
<td>C12702-04</td>
<td>A8407-05A</td>
<td>A8424-05A</td>
</tr>
<tr>
<td>C12702-11</td>
<td>A8407-18</td>
<td>A8424-18</td>
</tr>
<tr>
<td>C12702-12</td>
<td>A8407-05A</td>
<td>A8424-05A</td>
</tr>
<tr>
<td>C12703</td>
<td>A8407-05</td>
<td>A8424-05</td>
</tr>
<tr>
<td>C12703-01</td>
<td>A8407-05A</td>
<td>A8424-05A</td>
</tr>
<tr>
<td>C10508-01</td>
<td>A12855-01</td>
<td>A12855-02</td>
</tr>
</tbody>
</table>

High-speed type

This device can be used in a wide frequency range (up to 1 GHz).

Features
- High-speed light detection
- Flat frequency characteristics
- Compact and lightweight
- Single power supply operation

Applications
- OTDR
- Optical communication
- Laser radars
- FSO
- Optical rangefinders

<table>
<thead>
<tr>
<th>Type no.</th>
<th>Effective photosensitive area* (mm)</th>
<th>Internal APD</th>
<th>Cutoff frequency</th>
<th>Photoelectric conversion sensitivity M=100, λ=800 nm (V/W)</th>
<th>Minimum detection limit M=100, λ=800 nm (nW rms)</th>
<th>Temperature stability of gain 25 ± 10 °C (%)</th>
<th>Supply voltage (V)</th>
</tr>
</thead>
<tbody>
<tr>
<td>C5658</td>
<td>φ0.5</td>
<td>S12023-05</td>
<td>50 kHz, 1 GHz</td>
<td>2.50 × 10^5</td>
<td>16</td>
<td>±5</td>
<td>+12</td>
</tr>
</tbody>
</table>

* Area in which a typical gain can be obtained
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Photomultiplier tube modules
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